

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

Product Summary



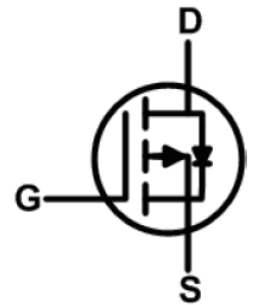
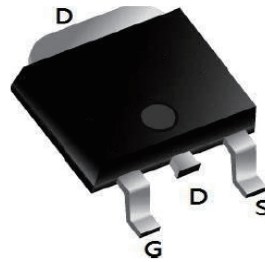
BVDSS	RDSON	ID
-30V	14.5mΩ	-50A

Description

The 50P03 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 50P03 meet the RoHS and Green Product requirement with full function reliability approved.

TO 252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Unit
		10s	Steady State	
V _{DS}	Drain-Source Voltage	-30		V
V _{GS}	Gate-Source Voltage	±25		V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-50		A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-32		
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-15	-9.6	
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -10V ¹	-12	-7.7	
I _{DM}	Pulsed Drain Current ²	-150		
EAS	Single Pulse Avalanche Energy ³	125		mJ
I _{AS}	Avalanche Current	-50		A
P _D @T _C =25°C	Total Power Dissipation ⁴	45		W
P _D @T _A =25°C	Total Power Dissipation ⁴	5	2	
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
R _{θJA}	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	25	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	2.8	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS} / \Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.0232	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-30A$	---	14.5	22	m Ω
		$V_{GS}=-4.5V, I_D=-15A$	---	22	32	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-30A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	9	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-15A$	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	8.7	---	
Q_{gd}	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-15A$	---	8	---	ns
T_r	Rise Time		---	73.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	61.8	---	
T_f	Fall Time		---	24.4	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	2215	---	pF
C_{oss}	Output Capacitance		---	310	---	
C_{rss}	Reverse Transfer Capacitance		---	237	---	

Thermal Data

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{Force Current}$	---	---	-50	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-150	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-15A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	19	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1\text{mH}, I_{AS}=-50A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Figure 1: Output Characteristics

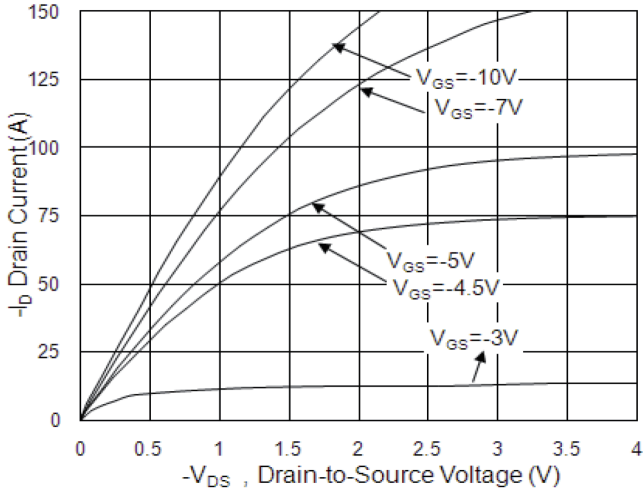


Figure 2: On-Resistance vs. G-S Voltage

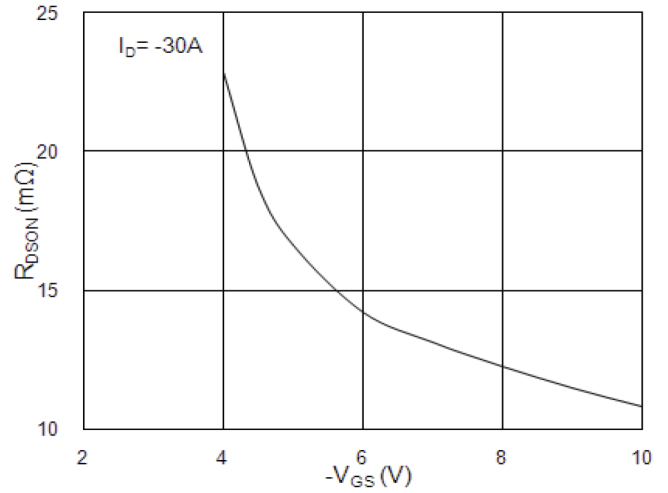


Figure 3: Forward Characteristics of Reverse

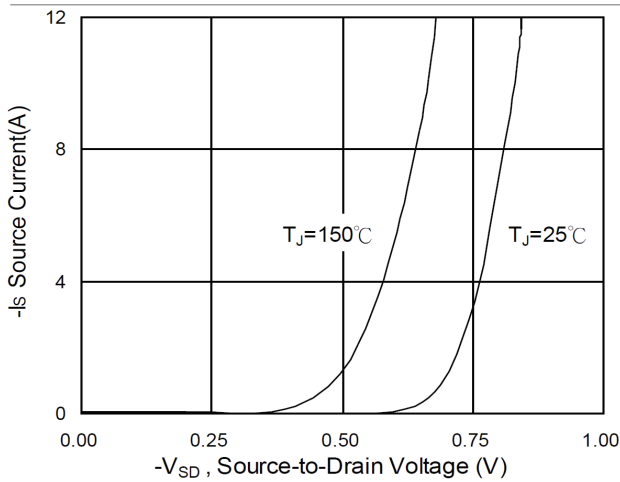


Figure 4: Gate-charge Characteristics

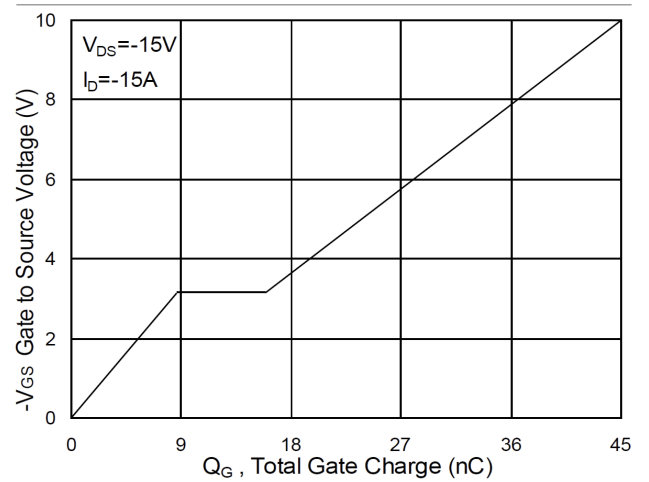


Figure 5: Normalized $V_{GS(th)}$ vs. T_J

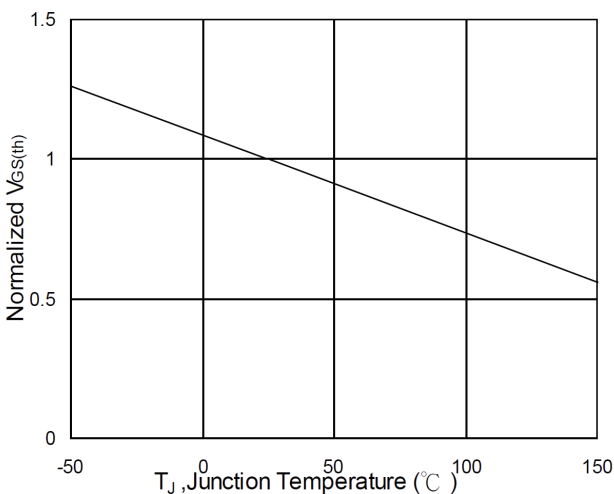
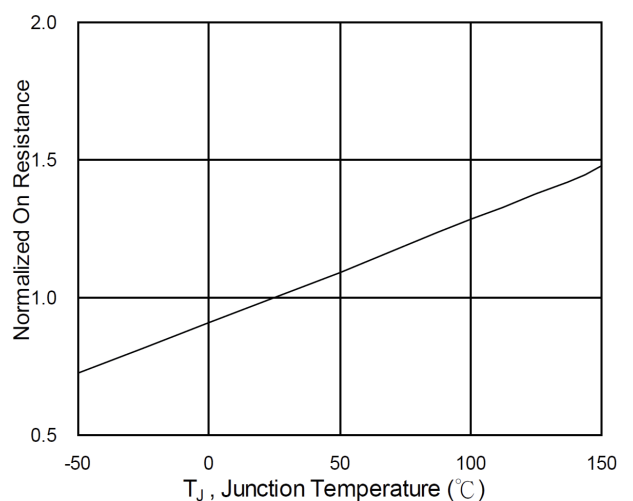


Figure 6: Normalized $R_{DS(on)}$ vs. T_J



Typical Performance Characteristics

Figure 7: Capacitance

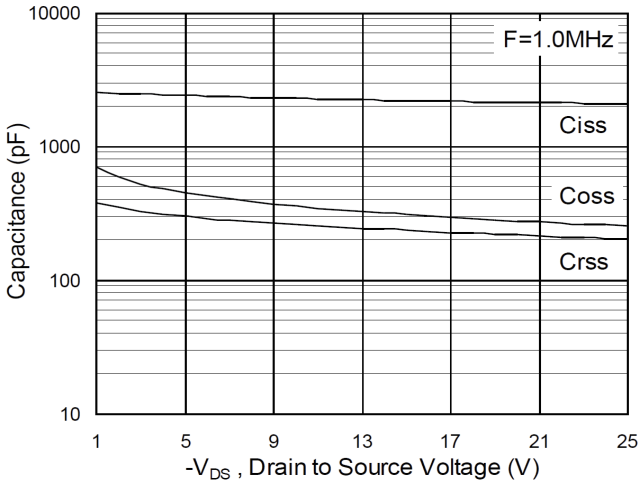


Figure 8: Safe Operating Area

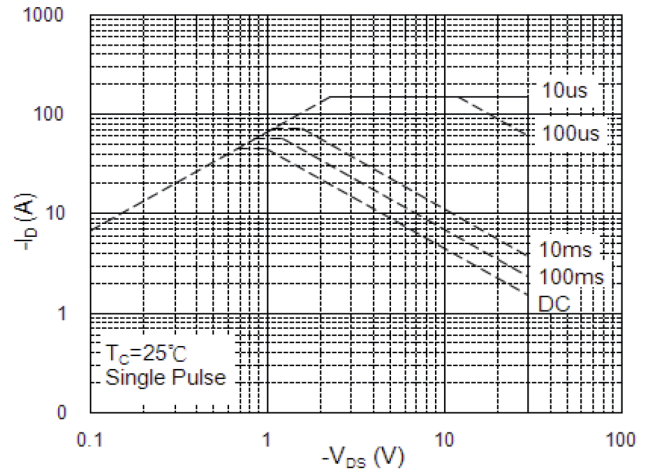


Figure 9: Normalized Maximum Transient Thermal Impedance

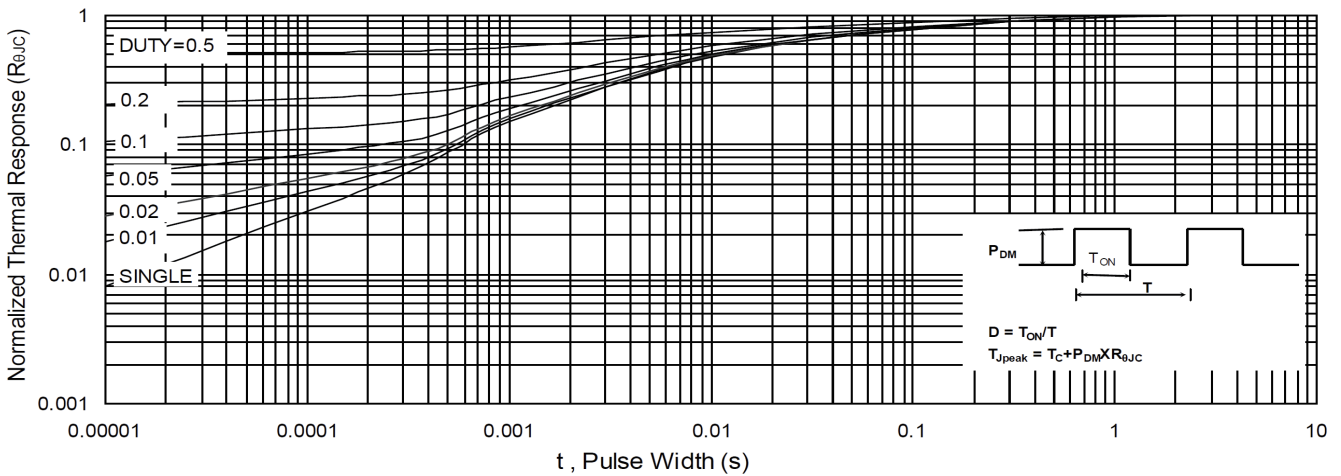


Figure 10: Switching Time Waveform

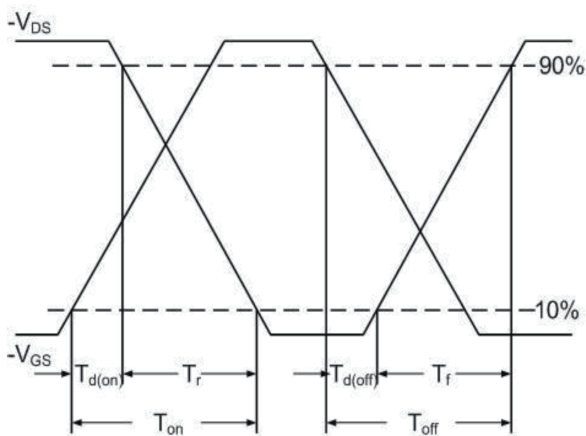
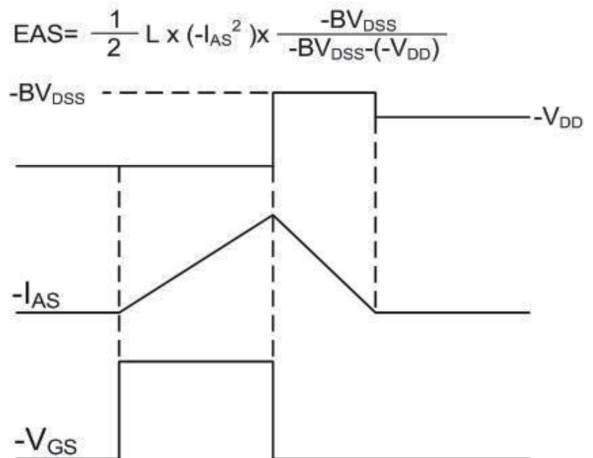
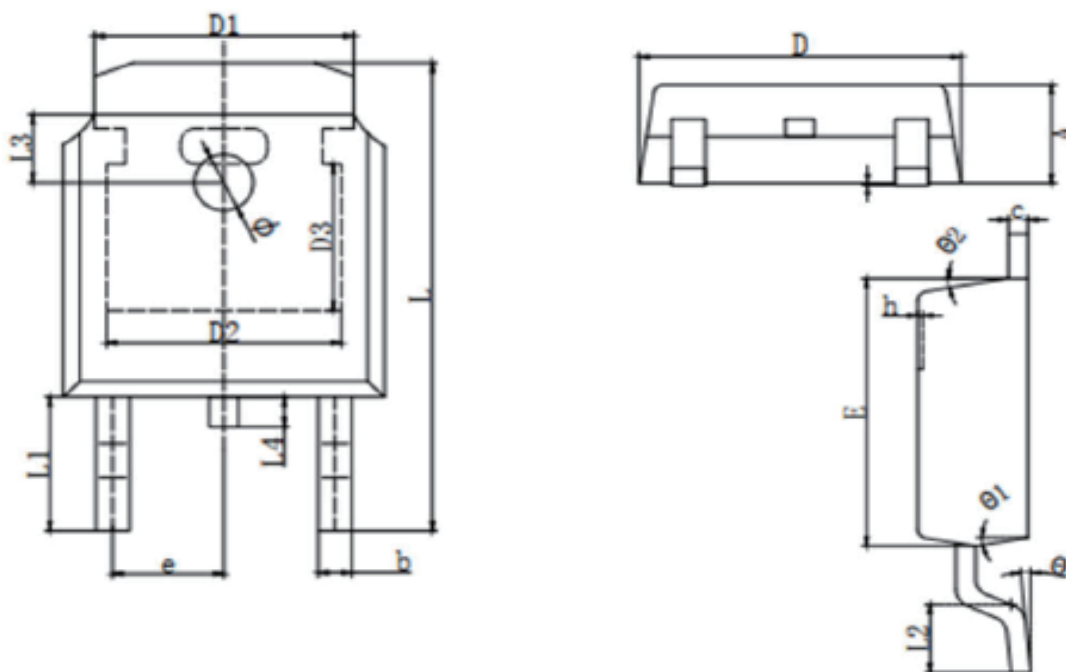


Figure 11: Unclamped Inductive Switching



TO-252 Package outline



SYMBOL	MILLIMETER		SYMBOL	MILLIMETER	
	MIN	MAX		MIN	MAX
A	2.200	2.400	h	0.000	0.200
A1	0.000	0.127	L	9.900	10.30
b	0.640	0.740	L1	2.888 REF	
c	0.460	0.580	L2	1.400	1.700
D	6.500	6.700	L3	1.600 REF	
D1	5.334 REF		L4	0.600	1.000
D2	4.826 REF		φ	1.100	1.300
D3	3.166 REF		θ	0°	8°
E	6.000	6.200	θ1	9° TYP2	
e	2.286 TYP		θ2	9° TYP	